

Supplementary Materials

Interface-engineered p-CsCu₂I₃/n-Ga₂O₃ nanowires heterojunctions for self-powered ultraviolet photodetection

Ruhan Luan,^a Fengzhou Zhao,^{*,b} Tao Chen, Daoping Peng,^a Xiao Zhang,^b Jixing Lin,^a Dengying Zhang,^b Taiping Lu^b and Lichun Zhang^{*,b}

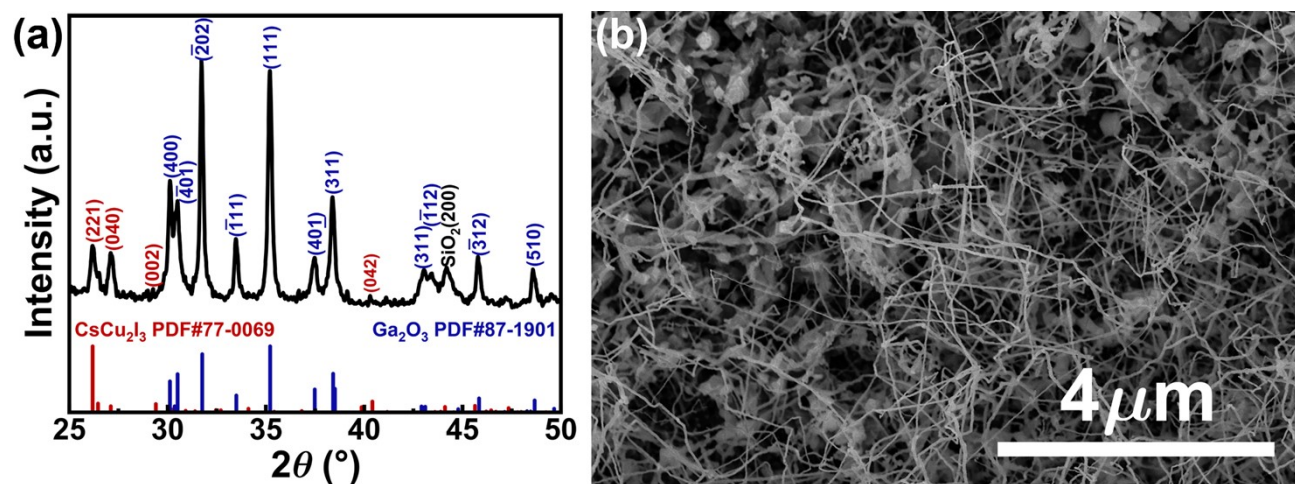


Figure S1 (a) XRD patterns of p-CsCu₂I₃/n-Ga₂O₃ NWs heterojunction without CuI interlayer. (b) Surface morphology of the p-CsCu₂I₃/n-Ga₂O₃ NWs heterojunction without CuI interlayer.

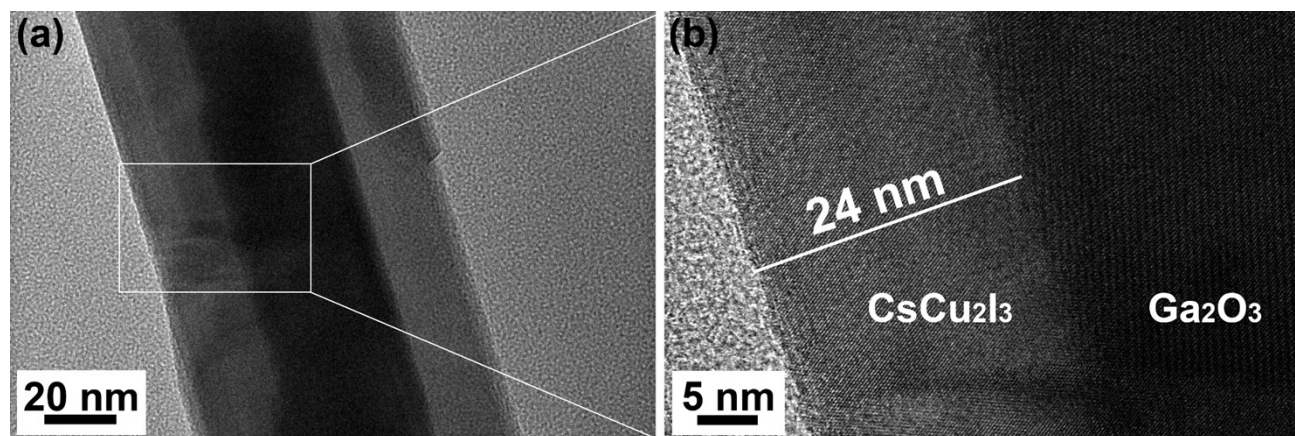


Figure S2 (a) A high-resolution TEM image of a CsCu₂I₃-coated Ga₂O₃ nanowire, and (b) an enlarged image of the region marked by the white box in (a).

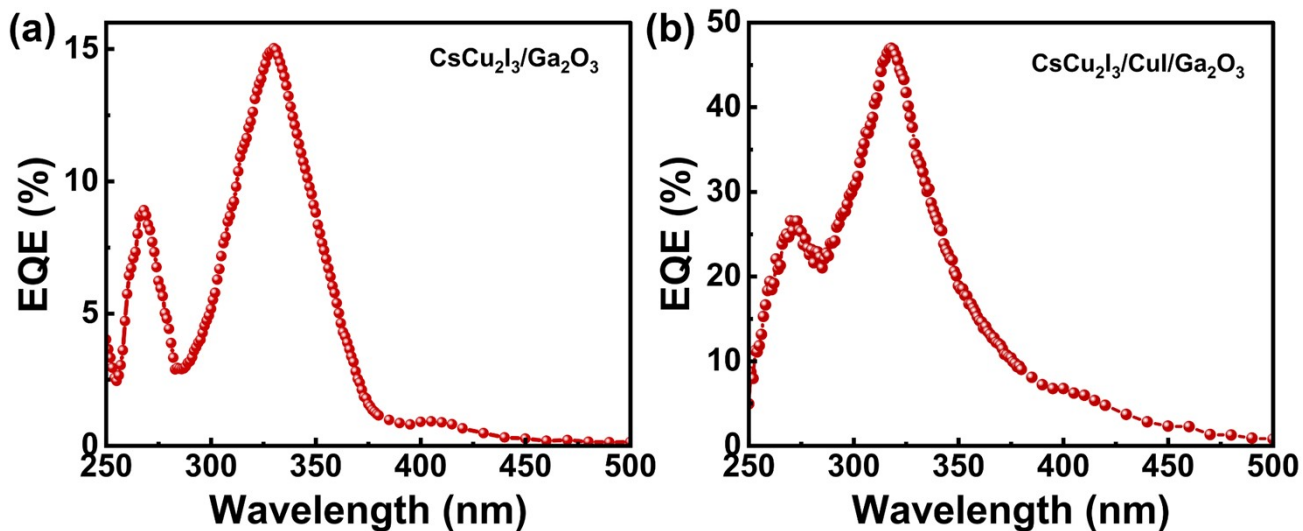


Figure S3 (a) EQE of CsCu₂I₃/Ga₂O₃ PD at 0 V, (b) EQE of CsCu₂I₃/CuI/Ga₂O₃ PD at 0 V.

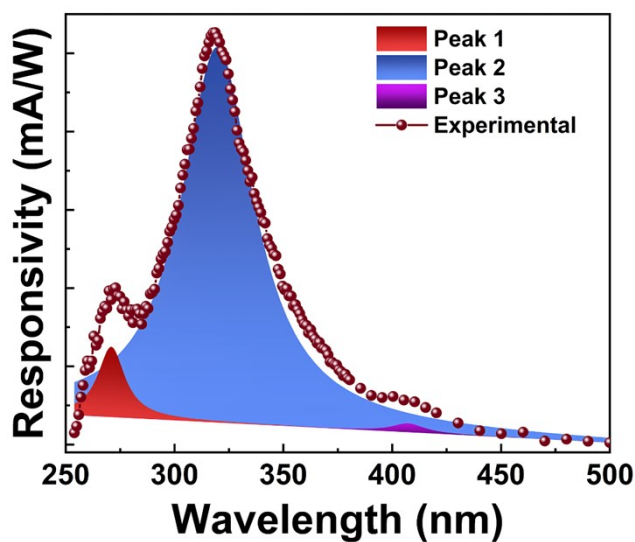


Figure S4 Spectral responsivity curve of the p-CsCu₂I₃/CuI/n-Ga₂O₃ NWs PD with Gaussian peak-deconvolution fitting.

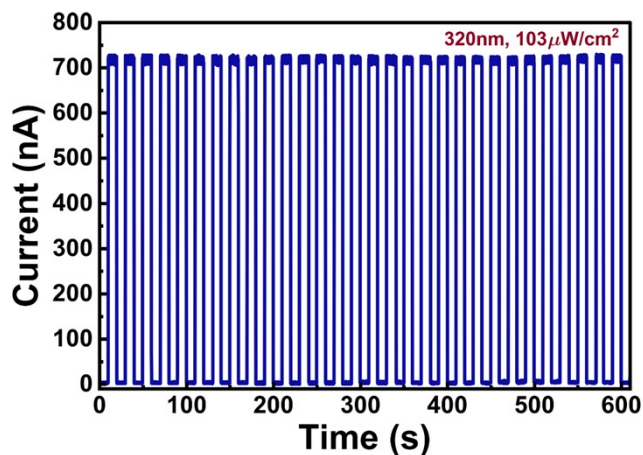


Figure S5 Cycling stability of the p-CsCu₂I₃/CuI/n-Ga₂O₃ NWs PD over 30 on/off cycles at 0 V bias under 320 nm irradiation.